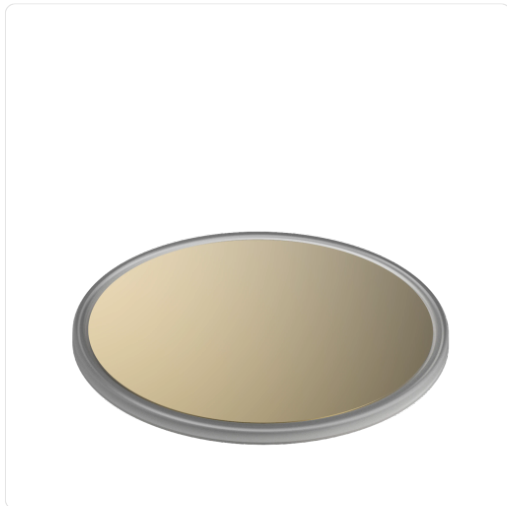


e Wafers



Specifications

Diameter, mm	100
Thickness, μm	175
Deviation from nominal value, μm	± 25
Crystallographic orientation, $^\circ$	(100)+6°; (111)
Conductivity type	P
Element	Ga
Resistivity	0.01–0.04 $\Omega\cdot\text{m}$
Charge carrier concentration, cm^{-3}	From $1\cdot 10^{18}$ to $4\cdot 10^{18}$
Dislocation density, cm^{-2}	< 500
Crystal orientation	(100)
Polishing	Single-sided
TTV minimum, μm	—
TTV minimum/standard, μm	до 15